



RRF015P03TL Information



For Reference Only

Part Number RRF015P03TL

Manufacturer Rohm Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 30V 1.5A TUMT3

Package 3-SMD, Flat Leads

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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RRF015P03TL Specifications

Manufacturer Part Number RRF015P03TL Manufacturer Rohm Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 3-SMD, Flat Leads Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 1.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ ImA Gate Charge (Qg) (Max) @ Vgs 6.4nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 230pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 320mW (Ta) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 3-SMD, Flat Leads Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 1.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs 6.4nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	Manufacturer Part Number	RRF015P03TL
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Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 1.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 6.4nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 230pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 320mW (Ta) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 1.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 6.4nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 230pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 320mW (Ta) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	Package	3-SMD, Flat Leads
Technology Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 1.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature MOSFET (Metal Oxide) 30V 4V, 10V 2.5V @ 1mA 6.4nC @ 10V 2.5V @ 1mA 2.5V @ 1mA 6.4nC @ 10V 2.30pF @ 10V 2.30pF @ 10V 4.20V 4.2	Series	-
Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 1.5A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 6.4nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 230pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 320mW (Ta) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 1.5A (Ta) 1.5A (10V)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature 4V, 10V 2.5V @ 1mA 6.4nC @ 10V 230pF @ 10V 230pF @ 10V 420V FET Feature - Power Dissipation (Max) 150°C (TJ)	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 6.4nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 230pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 320mW (Ta) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	Current - Continuous Drain (Id) @ 25°C	1.5A (Ta)
Gate Charge (Qg) (Max) @ Vgs 6.4nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 230pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 320mW (Ta) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	Drive Voltage (Max Rds On, Min Rds On)	4V, 10V
Input Capacitance (Ciss) (Max) @ Vds 230pF @ 10V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 320mW (Ta) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	Vgs(th) (Max) @ Id	2.5V @ 1mA
Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 320mW (Ta) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	Gate Charge (Qg) (Max) @ Vgs	6.4nC @ 10V
FET Feature - Power Dissipation (Max) 320mW (Ta) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	230pF @ 10V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs 160 mOhm @ 1.5A, 10V Operating Temperature 150°C (TJ)	FET Feature	-
Operating Temperature 150°C (TJ)	Power Dissipation (Max)	320mW (Ta)
	Rds On (Max) @ Id, Vgs	160 mOhm @ 1.5A, 10V
	Operating Temperature	150°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package TUMT3	Supplier Device Package	TUMT3
Package / Case 3-SMD, Flat Leads	Package / Case	3-SMD, Flat Leads
Report errors?		Report errors?

RRF015P03TL Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

RRF015P03TL Payment Methods



















RRF015P03TL Shipping Methods













If you have any question about RRF015P03TL, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com